Static RAM
as long as power is applied data is retained.

\[ V_{DD} \]
\[ \frac{V_{DD}}{2} \]

\[ V_{DD} \]
\[ 0 \]

\[ V_{DD} \]
\[ 0 \]

Row

Bit

Overline Bit
6T-SEAM

\[ V_{DD} \]

\[ V_{DD} \]

\[ \frac{V_{DD}}{2} \]

\[ I_{on} = \frac{W}{L} \cdot I_{o} \]

\[ I_{on} = \frac{W}{L} \cdot I_{o} \]

\[ I_{o} = \frac{W}{L} \cdot I_{o} \]

\[ P = (I_{on} + I_{op}) \cdot \frac{V_{DD}}{1V} \]

\[ V_{OS} = \sqrt{V_{DD}} \]

\[ V_{OS} = \sqrt{V_{DD}} \]

\[ \frac{V_{DD}}{2} \]
Flash Memory

VDS bin

I_D

Native or Erased state

Row line

SLC

Event occurrence

UNIT
$C_{tot} = 200 \text{ pF (OEA)}$

$= 5 \text{ pF}$

$R_{bit} = 1 \text{ M\Omega}$